查询PMEG6010CEH PMEG6010CEH; PMEG6010CEJ

1 A very low V_F MEGA Schottky barrier rectifiers Rev. 02 — 27 March 2007 Pro

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small and flat lead Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	Configuration	
	NXP	JEITA	
PMEG6010CEH	SOD123F	-	single
PMEG6010CEJ	SOD323F	SC-90	single
Features			WWW.DZSC.COM

1.2 Features

- Forward current: $I_F \le 1 A$
- Reverse voltage: $V_R \le 60 V$
- Very low forward voltage
- Small and flat lead SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	T _{sp} ≤ 55 °C	-	-	1	A
V _R	reverse voltage		-	-	60	V
V _F	forward voltage	I _F = 1 A	<u>[1]</u> _	570	660	mV

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.





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2. Pinning information

Table 3.	Pinning	
Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 <u>−</u> 2 1 <u>−</u> 2 <i>sym001</i> 001aab540

[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Orderin	g information	1	
Type number	Package		
	Name	Description	Version
PMEG6010CEH	-	plastic surface-mounted package; 2 leads	SOD123F
PMEG6010CEJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

4. Marking

Table 5.	Marking codes	
Type num	ıber	Marking code
PMEG601	IOCEH	CA
PMEG601	IOCEJ	EQ

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5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage			-	60	V
l _F	forward current	$T_{sp} \le 55 \ ^{\circ}C$		-	1	А
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$		-	7	А
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms				
	PMEG6010CEH			-	9	А
	PMEG6010CEJ			-	10	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PMEG6010CEH		[1]	-	375	mW
			[2]	-	830	mW
	PMEG6010CEJ		[1]	-	350	mW
			[2]	-	830	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PMEG6010CEH		[2] _	-	330	K/W
			[3] _	-	150	K/W
	PMEG6010CEJ		[2] _	-	350	K/W
			[3] _	-	150	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[4]</u>			
	PMEG6010CEH		-	-	60	K/W
	PMEG6010CEJ		-	-	55	K/W

 For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[4] Soldering point of cathode tab.

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7. Characteristics

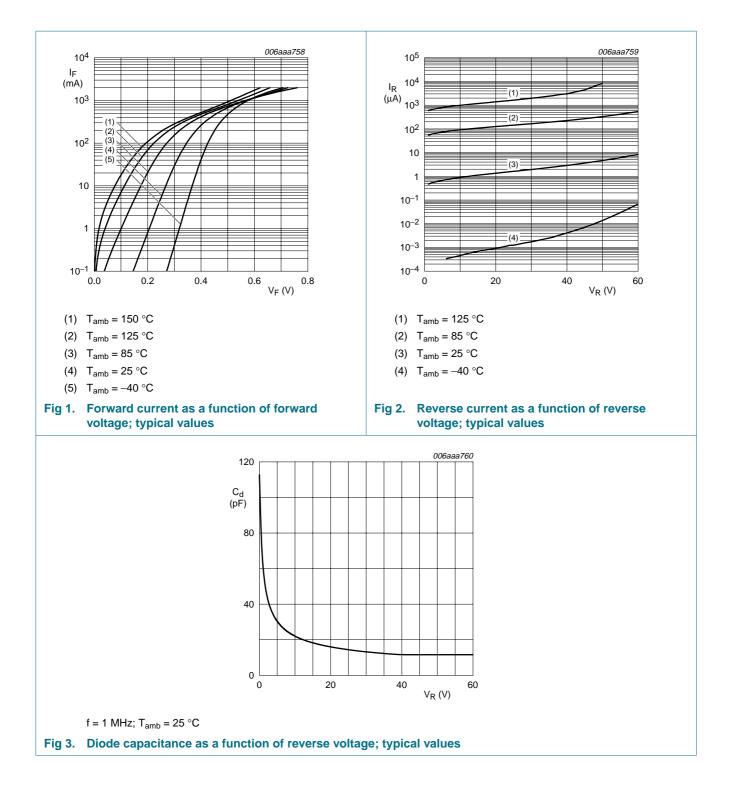
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage		<u>[1]</u>			
		I _F = 1 mA	-	210	250	mV
		I _F = 10 mA	-	270	310	mV
		I _F = 100 mA	-	350	400	mV
		I _F = 500 mA	-	460	530	mV
		I _F = 700 mA	-	510	580	mV
		I _F = 1 A	-	570	660	mV
I _R reverse current	reverse current	V _R = 5 V	-	0.8	-	μA
		V _R = 10 V	-	1.1	-	μA
		V _R = 60 V	-	11	50	μA
C _d	diode capacitance	$V_{R} = 1 V; f = 1 MHz$	-	60	68	pF

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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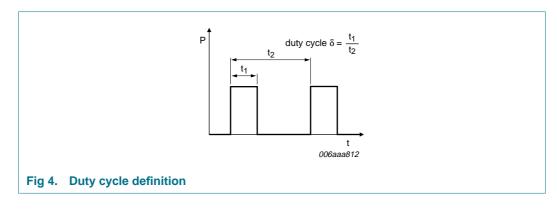
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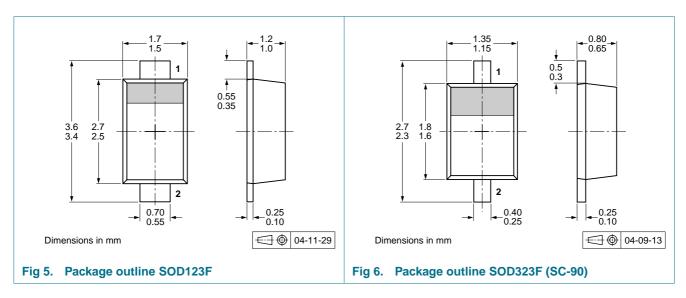
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8. Test information



9. Package outline



10. Packing information

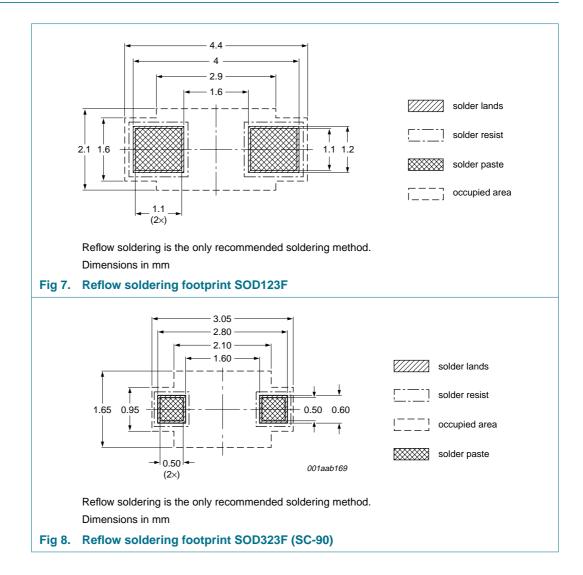
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[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG6010CEH_PMEG6010CEJ_ 2	20070327	Product data sheet	-	PMEG6010CEJ_1		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
	 Type numbe 	r PMEG6010CEH added				
	Section 1.1 '	"General description": am	ended			
	• Table 1 "Pro	duct overview": added				
	• Table 7 "The	rmal characteristics": Tab	le note 1 amended			
	 Section 8 "Te 	est information": added				
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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Date of release: 27 March 2007 Document identifier: PMEG6010CEL_PMEG6010CEJ_2

